

1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



Product data sheet

1. General description

Silicon Carbide Schottky diode in a SOD59A (TO-220AC) plastic package, designed for high frequency switched-mode power supplies.

2. Features and benefits

- Highly stable switching performance
- High forward surge capability I_{FSM}
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom/Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED/OLED TV
- Motor Drives

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage			-	-	650	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} \leq 124 °C; square-wave pulse; Fig. 1; Fig. 2		-	-	6	Α
T _j	junction temperature			-	-	175	°C
Static characte	Static characteristics						
V _F	forward voltage	I _F = 6 A; T _j = 25 °C; <u>Fig. 4</u>		-	1.5	1.7	V





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic characteristics						
Q _r	recovered charge	$I_F = 6 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 500 \text{ A/}\mu\text{s}$;	-	10	-	nC
		T _j = 25 °C; <u>Fig. 5</u>				

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode	7 0 5	001aaa020
mb	mb	mounting base; connected to cathode	TO-220AC (SOD59A)	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
NXPSC06650	TO-220AC	Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59A

7. Marking

Table 4. Marking codes

Type number	Marking code
NXPSC06650	NXPSC06650

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	650	V
V_{RWM}	crest working reverse voltage		-	650	V
V _R	reverse voltage	DC	-	650	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 124 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u>	-	6	A
I _{FRM}	repetitive peak forward current	$\bar{\delta}$ = 0.5; t _p = 25 μs; T _{mb} ≤ 124 °C; square-wave pulse	-	12	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	36	A
		t_p = 10 μ s; $T_{j(init)}$ = 25 °C; square-wave pulse	-	310	A
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-	175	°C

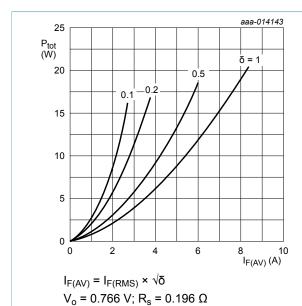


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

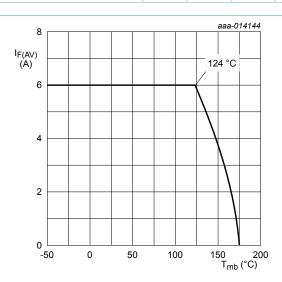


Fig. 2. Forward current as a function of mounting base temperature; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 3	-	-	2.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

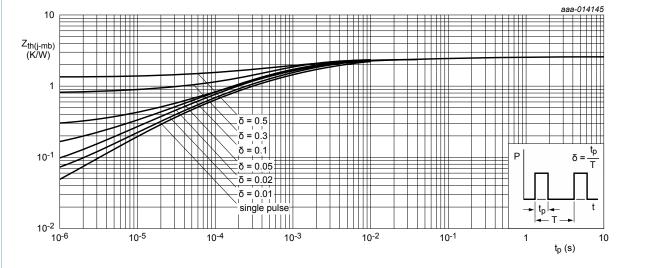


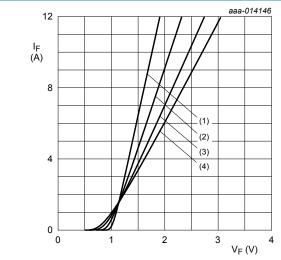
Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse duration

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Mir	Тур	Max	Unit	
Static characteristics							
V _F	forward voltage	I _F = 6 A; T _j = 25 °C; <u>Fig. 4</u>	-	1.5	1.7	V	
		I _F = 6 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.8	2.1	V	
I _R revers	reverse current	V _R = 650 V; T _j = 25 °C	-	-	200	μΑ	
		V _R = 650 V; T _j = 150 °C	-	-	640	μA	
Dynamic ch	naracteristics			'			
Q _r	recovered charge	$I_F = 6 \text{ A}; dI_F/dt = 500 \text{ A/}\mu\text{s}; V_R = 400 \text{ V};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 5}}{200}$	-	10	-	nC	
C _d diode capacitan		f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	190	-	pF	
		$f = 1 \text{ MHz}; V_R = 300 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	23	-	pF	
		f = 1 MHz; V _R = 600 V; T _j = 25 °C	-	19	-	pF	



 V_o = 0.766 V; R_s = 0.196 Ω

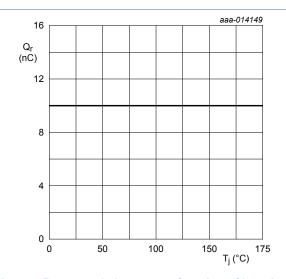
(1) T_i = 25 °C; typical values

(2) T_i = 100 °C; typical values

(3) $T_j = 150$ °C; typical values

(4) T_i = 175 °C; typical values

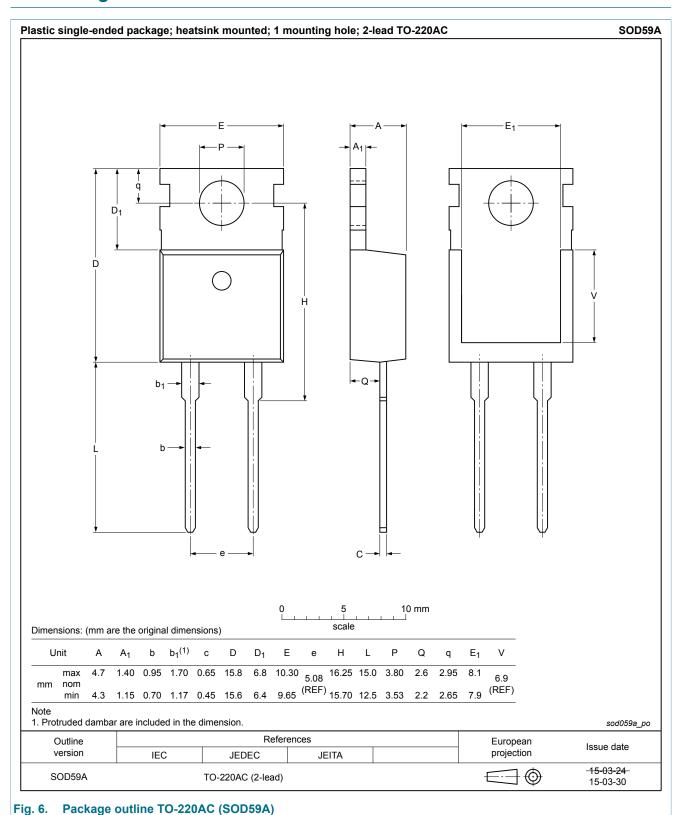




ig. 5. Recovered charge as a function of junction temperature

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11. Package outline



NXPSC06650

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12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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